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TRANSMITTAL FORM (to be used for all correspondence after initial)	Application Number Filing Date First Named Inventor	Approved for use through 04/30/2003. OMB 0651-0031 and Trademark Office; U.S. DEPARTMENT OF COMMERCE on of information unless it displays a valid OMB control number. 10/733,181 12/10/2003 Manning et al. 2834 Unknown
Total Number of Pages in This Submission	7	M155-55a2
Fee Transmittal Form Fee Attached Amendment/Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53	Drawing(s) Licensing-related Papers Petition Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence Address Terminal Disclaimer Request for Refund CD, Number of CD(s) Remarks	After Allowance Communication to a Technology Center (TC) Appeal Communication to Board of Appeals and Interferences Appeal Communication to TC (Appeal Notice, Brief, Reply Brief) Proprietary Information
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Firm or David G. Latwesen, Ph.D. Wells St. John, P.S. Individual Signature Date CI I hereby certify that this correspondence is being far	, Reg. No. 38,533 ERTIFICATE OF TRANSMISSION	I/MAILING with the United States Postal Service with sufficient postage as
Signature	Tidal	Date 5-24-05

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

atent Application Serial No	10/733,181
Filing Date	December 10, 2003
Inventor	H. Montgomery Manning et al.
Assignee	Micron Technology, Inc.
Group Art Unit	2812
Examiner	Unknown
Attorney Docket No	MI22-2295
Customer No.	
Title: Semiconductor Constructions, and	Methods of Forming Capacitor Devices

ie: Semiconductor Constructions, and Methods of Forming Capacitor Devices

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

EV 550717282

This Supplemental Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing of a first Office Action on the merits, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

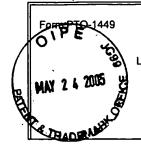
Respectfully submitted,

Dated: ___//___

David G. Latwesen, Ph.D.

Reg. No. 38,533

By:



U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. MI22-2295

SERIAL NO. 10/733,181

LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)

APPLICANT: H. Montgomery Manning et al.

GROUP 2812

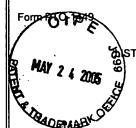
FILING DATE December 10, 2003

U.S. PATEN	U.S. PATENT DOCUMENTS							
*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA			FV550717	2 8	2	-	
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FOREIGN PATENT DOCUMENTS									
		Document	Date	Country	Class	Class Subclass Transl		ation	
		Number					Yes	No	
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EXAMINER		DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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SERIAL NO. 10/733,181

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APPLICANT: H. Montgomery Manning et al.

FILING DATE December 10, 2003

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